



TM05N10MI

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = 100V$ $I_D = 5.0A$

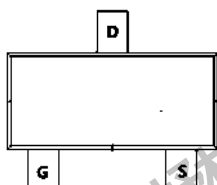
$R_{DS(ON)} = 105(\text{typ.})m\Omega @ V_{GS}=10V$

100% UIS Tested

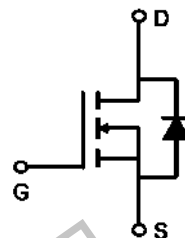
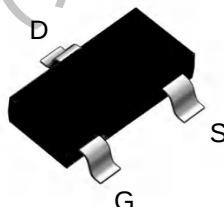
100% R_g Tested



MI:SOT-23-3L



Marking: 1005



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	5.0	A
$I_D @ T_A=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$	4.4	A
I_{DM}	Pulsed Drain Current	26	A
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	48	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	---	$^\circ\text{C/W}$

TM05N10MI

N-Channel Enhancement Mosfet

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	107	-	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V,	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	2.0	3.0	V
RDS(on)	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =4A	-	105	125	mΩ
		V _{GS} =4.5V, I _D =3A	-	110	145	mΩ
Ciss	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	610	-	pF
Coss	Output Capacitance		-	40	-	pF
Crss	Reverse Transfer Capacitance		-	25	-	pF
Qg	Total Gate Charge	V _{DS} =30V, I _D =10A, V _{GS} =10V	-	12	-	nC
Qgs	Gate-Source Charge		-	2.2	-	nC
Qgd	Gate-Drain("Miller") Charge		-	2.5	-	nC
td(on)	Turn-on Delay Time	V _{DS} =30V, I _D =5A, R _G =1.8Ω, V _{GS} =10V	-	7	-	ns
t _r	Turn-on Rise Time		-	5	-	ns
td(off)	Turn-off Delay Time		-	16	-	ns
t _f	Turn-off Fall Time		-	6	-	ns
IS	Continuous Source Current	V _G =V _D =0V, Force Current	-	-	5	A
ISM	Pulsed Source Current		-	-	40	A
VSD	Diode Forward Voltage	V _{GS} =0V, I _S =10A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F =10A, dI/dt=100A/μs	-	21	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	21	-	nC



TM05N10MI

N-Channel Enhancement Mosfet

Typical Characteristics

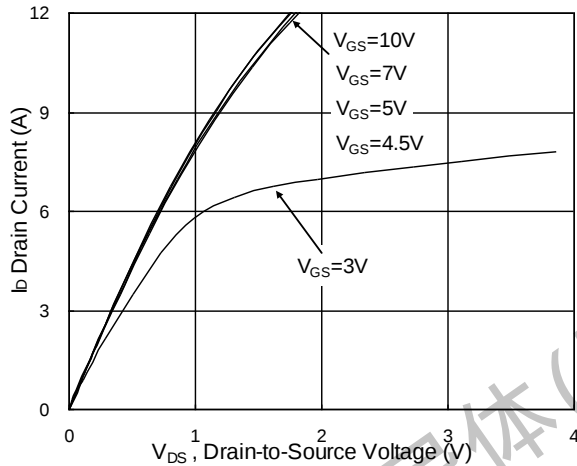


Fig.1 Typical Output Characteristics

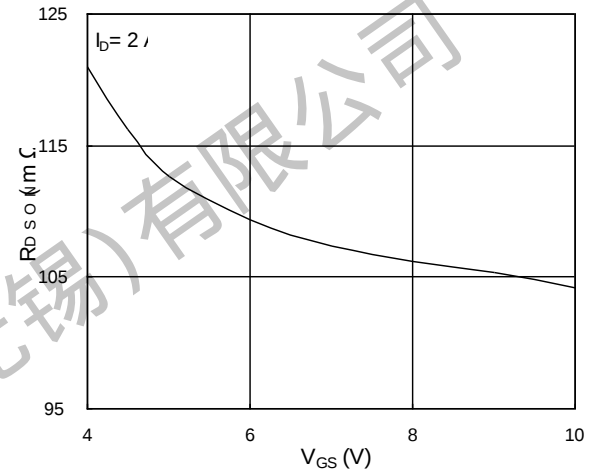


Fig.2 On-Resistance vs. Gate-Source

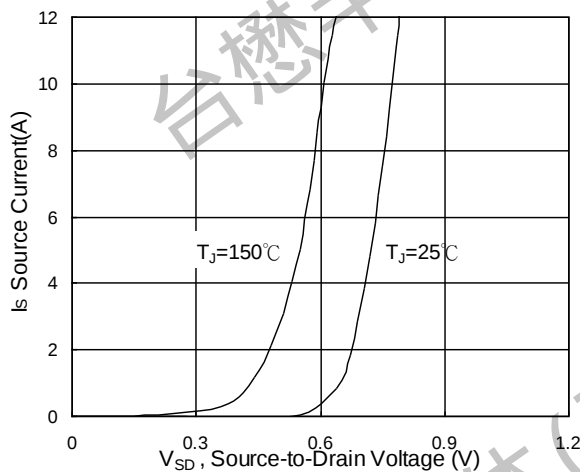


Fig.3 Forward Characteristics Of Reverse

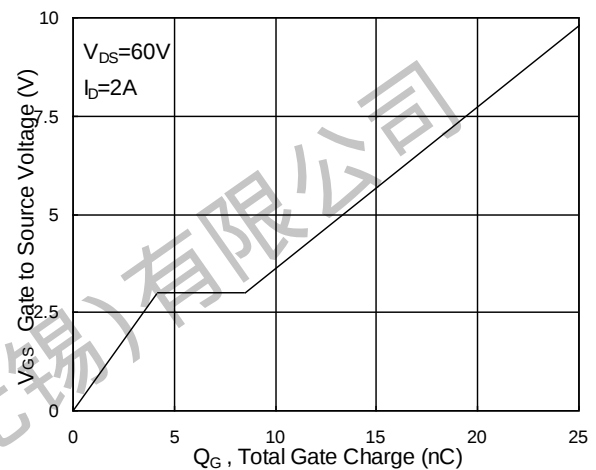


Fig.4 Gate-Charge Characteristics

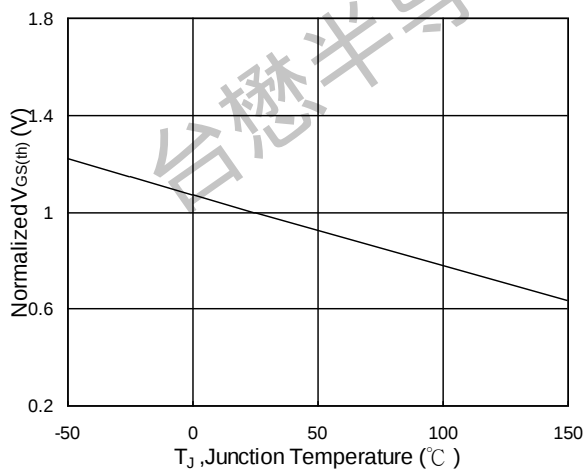


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

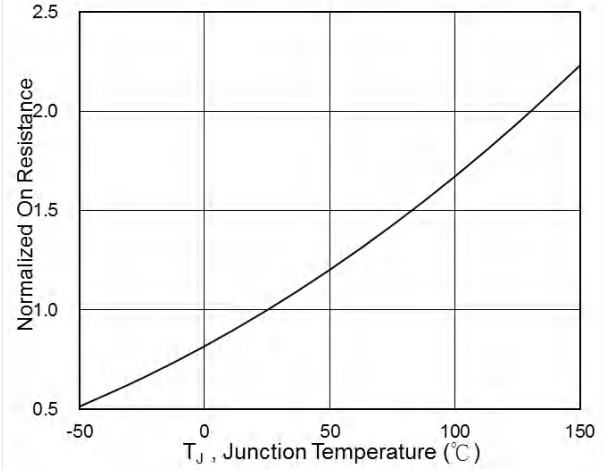


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

TM05N10MI

N-Channel Enhancement Mosfet

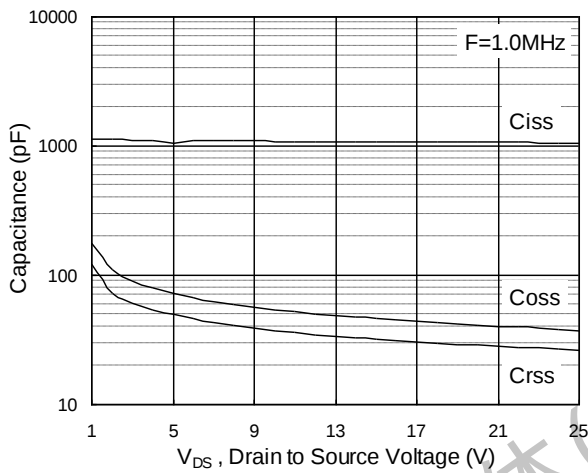


Fig.7 Capacitance

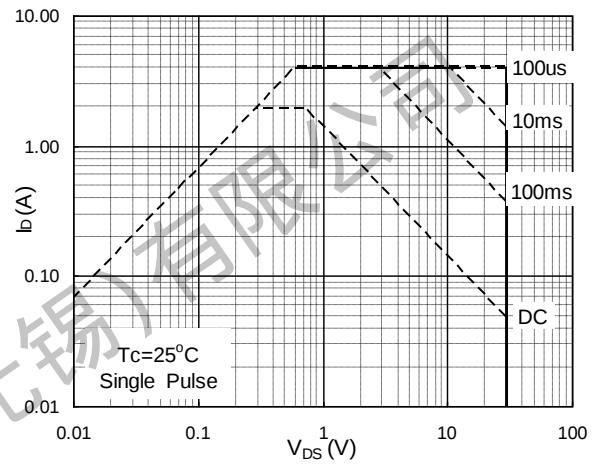


Fig.8 Safe Operating Area

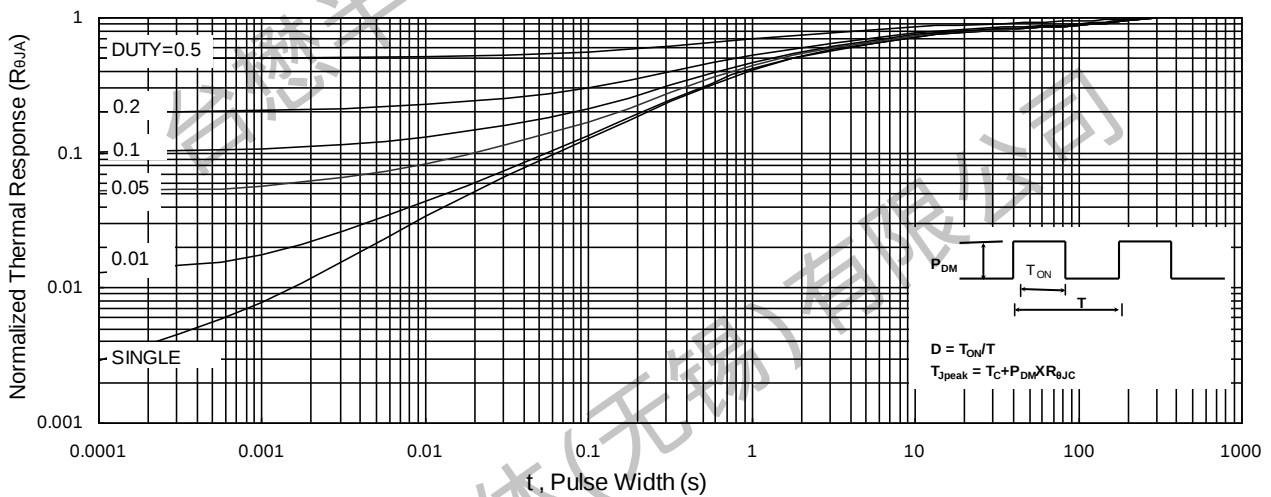


Fig.9 Normalized Maximum Transient Thermal Impedance

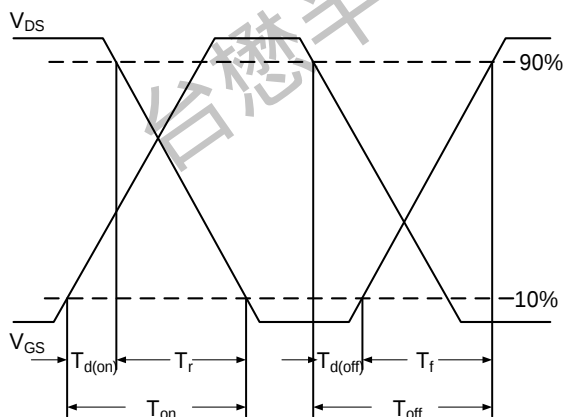


Fig.10 Switching Time Waveform

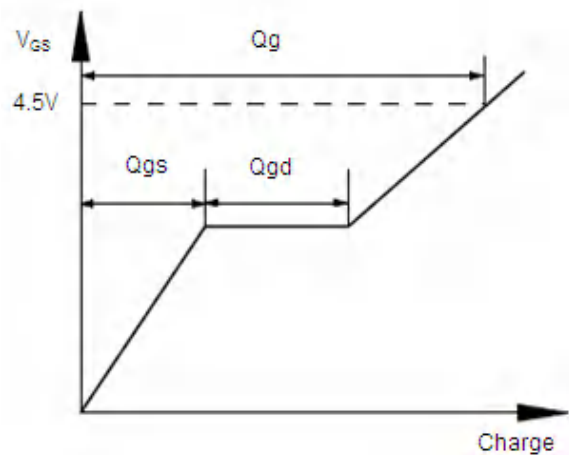
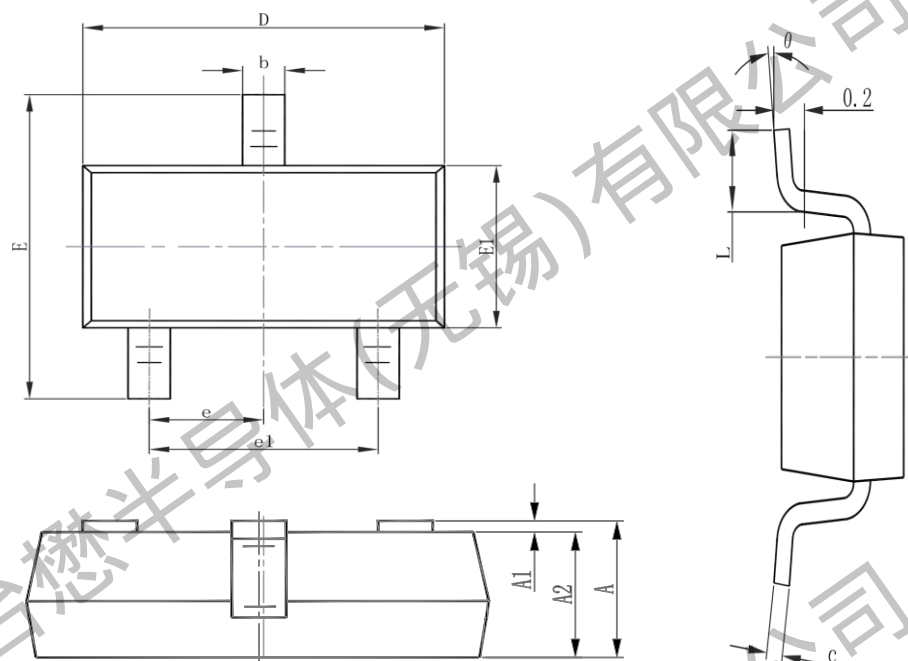


Fig.11 Gate Charge Waveform

TM05N10MI

N-Channel Enhancement Mosfet

Package Mechanical Data:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

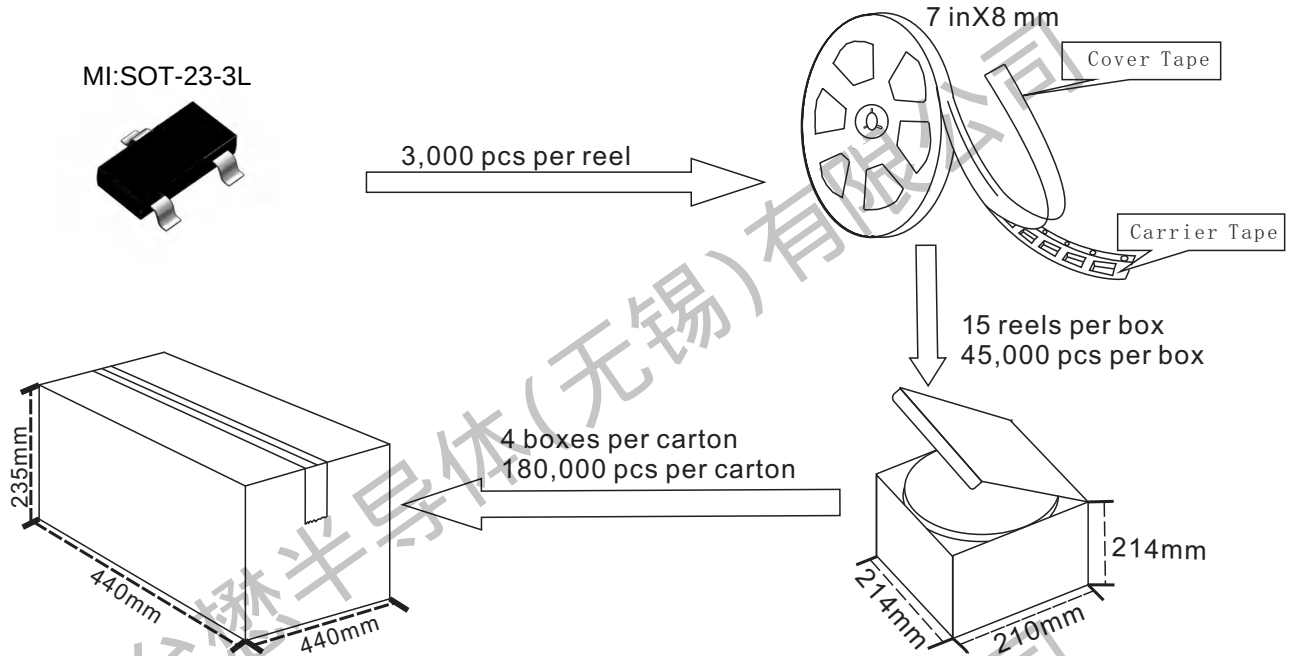


TM05N10MI

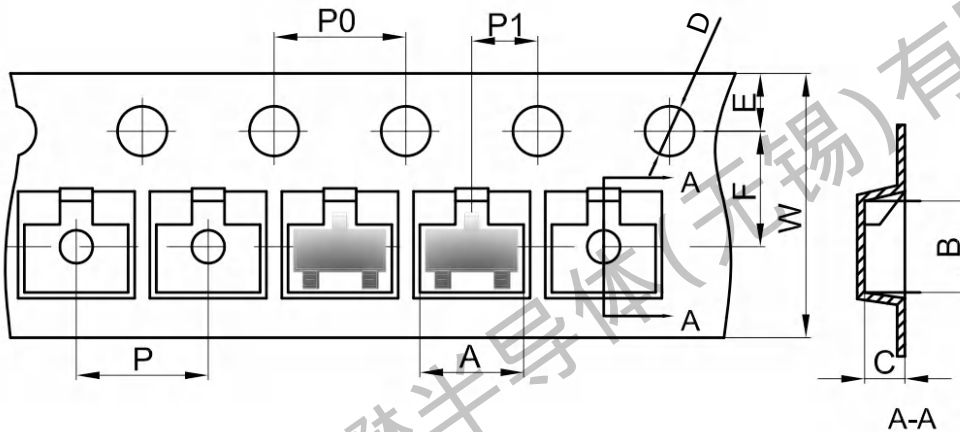
N-Channel Enhancement Mosfet

SOT-23-3L Packing

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)



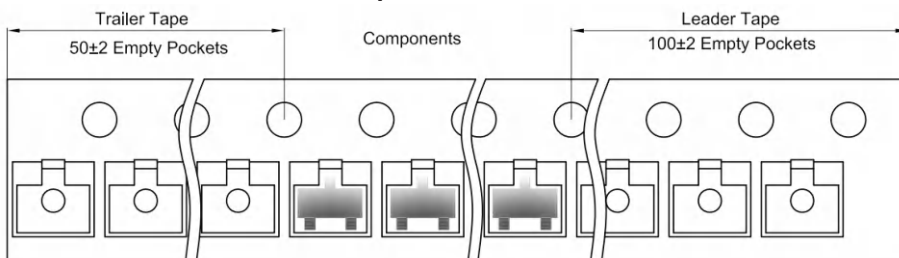
SOT-23-3L Embossed Carrier Tape



Dimensions are in millimeter

Pkg type	A	B	C	D	E	F	P0	P	P1	W
SOT-23-3L	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-3L Tape Leader and Trailer



Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2023.08.06	23.08	Original	